TECHNICAL DATA
DATASHEET 759 REV. A

SILICON SCHOTTKY RECTIFIER DIE

Applications:

- **Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode**

Features:

- **Ultra low Reverse Leakage Current**
- **Soft Reverse Recovery at Low and High Temperature**
- **Very Low Forward Voltage Drop**
- **Low Power Loss, High Efficiency**
- **High Surge Capacity**
- **Guard Ring for Enhanced Durability and Long Term Reliability**
- **Guaranteed Reverse Avalanche Characteristics**
- **Electrically / Mechanically Stable during and after Packaging**

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	60	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, Sine pulse (1)	570	A
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 30A, Pulse, T_J = 25 °C	0.68	V
	V_{F2}	@ 30A, Pulse, T_J = 125 °C	0.62	V
Reverse Current	I_{R1}	@V_R = 60V, Pulse, T_J = 25 °C	0.8	mA
	I_{R2}	@V_R = 60V, Pulse, T_J = 125 °C	60	mA
Junction Capacitance	C_T	@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz, V_{SIG} = 50mV (p-p)	1600	pF

(1) in SHD package

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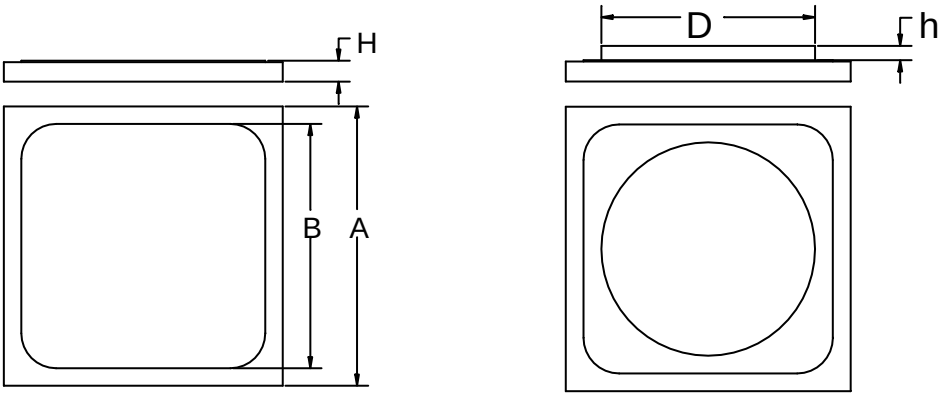
Mechanical Dimensions: In Inches (mm)



Bottom side metalization Ag - 5 kÅ minimum.

Top side metalization

A = Al - 25 kÅ minimum

B = Ag -30 kÅ minimum

C= Au plated Ni-Moly disc with bare edge

Bottom side is cathode, top side is anode.

A	B	D	H	h
0.175 ± 0.003 (4.45 ± 0.077)	0.163 ± 0.003 (4.14 ± 0.077)	0.120 ± 0.003	0.0105 ± 0.001, for Al top 0.0155 ± 0.001, for Ag top	.011± 0.001